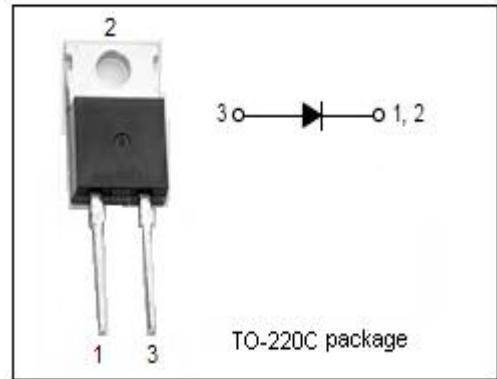


Ultra fast Rectifier

DSEI20-12A

FEATURES

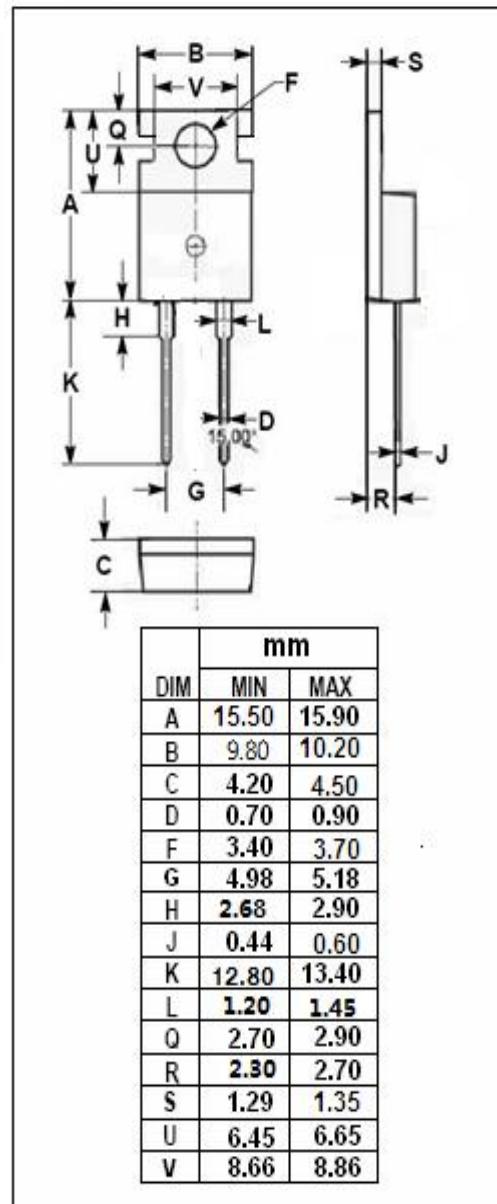
- With TO-220 packaging
- Metal silicon junction, majority carrier conduction
- Low leakage current
- Low power loss, high efficiency
- High current capability and low forward voltage drop
- Guardring for overvoltage protection
- High surge capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation


APPLICATIONS

- Switching power supply
- High frequency inverters
- Freewheeling diodes
- Reverse battery protection
- Polarity protection applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNI T
V_{RRM}	Peak Repetitive Reverse Voltage		
V_{RMS}	RMS Voltage	1200	V
V_R	DC Blocking Voltage		
$I_{F(AV)}$	Average Rectified Forward Current @ $T_c=125^\circ\text{C}$	17	A
I_{FRM}	Repetitive Peak Surge Current (Square Wave, 20kHz)	70	A
I_{FSM}	Nonrepetitive Peak Surge Current 8.3 ms single half sine-wave superimposed on rated load conditions;One shot	140	A
P_D	Maximum Power Dissipation	78	W
T_j	Junction Temperature	-55~175	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~175	$^\circ\text{C}$



Ultra fast Rectifier**DSEI20-12A****THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case	2.0	°C/W

ELECTRICAL CHARACTERISTICS (Pulse Test: Pulse Width=300 μ s,Duty Cycle≤1%)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V _F	Maximum Instantaneous Forward Voltage	I _F = 12A ;T _c = 25°C I _F = 12A ;T _c = 125°C	2.15 1.87	V
I _R	Maximum Instantaneous Reverse Current	V _R = rated V _{RRM}	0.75	mA
t _{rr}	Maximum Reverse Recovery Time	I _F =1A;di _f /dt=100A/ μ s;V _R =30V	60	ns